NSN 5961-01-111-5863

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View Online at https://aerobasegroup.com/nsn/5961-01-111-5863 **Inclosure Material:** Metal all transistor **Overall Length:** 1.563 inches all transistor **Overall Height:** 0.350 inches all transistor Overall Width: 1.050 inches all transistor **Mounting Facility Quantity:** 2 all transistor **Internal Configuration:** Junction contact all transistor Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-2o4aa all transistor **Internal Junction Configuration:** Npn all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Unthreaded hole all transistor **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 350.0 breakdown voltage, collector-to-emitter, base open all transistor **Current Rating Per Characteristic:** 8.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 125.0 watts small-signal input power, common-collector absolute all transistor **Transfer Ratio:** 12.0 static forward current transfer ratio, common-emitter all transistor and 60.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction all transistor **Terminal Type And Quantity:** 2 pin all transistor and 1 case all transistor Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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